

[Abstract]

The present invention addresses the problem of providing a silicon nitride etching liquid composition which is capable of selectively etching Si_3N_4 with a practical etching selectivity with respect to SiO_2 , while suppressing regrowth of SiO_2 , and which is also capable of suppressing pattern collapse of an SiO_2 film in the production of a 3D nonvolatile memory cell. A silicon nitride etching liquid composition for producing a 3D nonvolatile memory cell, which contains phosphoric acid, one or more silane coupling agents and water, but which does not contain ammonium ions.

FIG 3